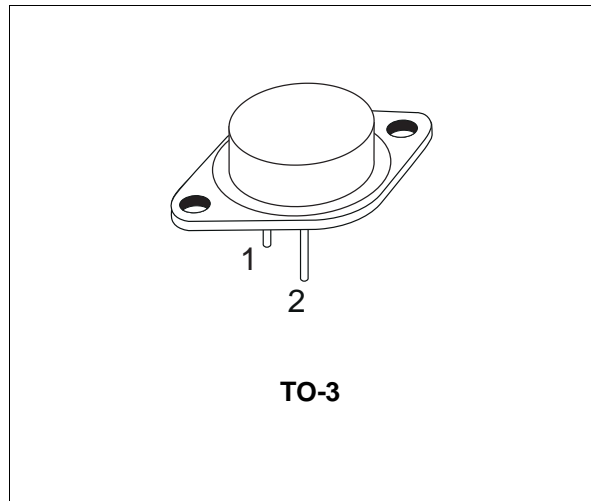


SILICON NPN TRANSISTOR

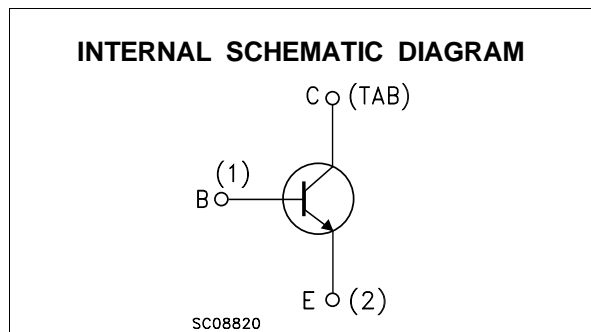
- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR

DESCRIPTION

The 2N3055 is a silicon epitaxial-base NPN transistor in Jedec TO-3 metal case. It is intended for power switching circuits, series and shunt regulators, output stages and high fidelity amplifiers.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	100	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} = 100\Omega$)	70	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	60	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	15	A
I_B	Base Current	7	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$	115	W
T_{stg}	Storage Temperature	-65 to 200	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	200	$^\circ\text{C}$

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.5	°C/W
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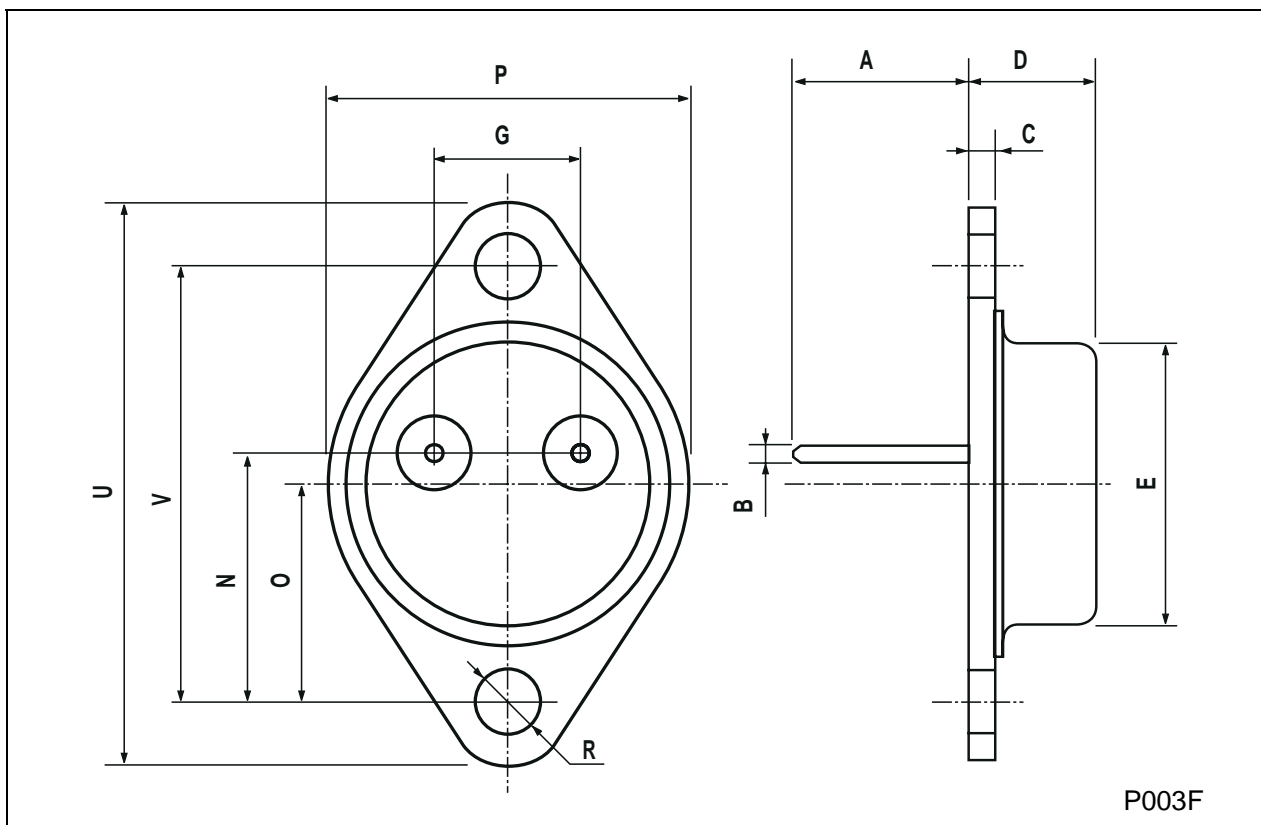
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 100 V V _{CE} = 100 V T _j = 150 °C			1 5	mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 30 V			0.7	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V			5	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 200 mA	60			V
V _{CER(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 200 mA R _{BE} = 100 Ω	70			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 4 A I _B = 400 mA I _C = 10 A I _B = 3.3 A			1 3	V V
V _{BE*}	Base-Emitter Voltage	I _C = 4 A V _{CE} = 4 V			1.5	V
h _{FE*}	DC Current Gain	I _C = 0.5 A V _{CE} = 4 V Group 4 I _C = 0.5 A V _{CE} = 4 V Group 5 I _C = 0.5 A V _{CE} = 4 V Group 6 I _C = 0.5 A V _{CE} = 4 V Group 7 I _C = 4 A V _{CE} = 4 V I _C = 10 A V _{CE} = 4 V	20 35 60 120 20 5		50 75 145 250 70	
h _{FE1/h_{FE1*}}	DC Current Gain	I _C = 0.5 A V _{CE} = 4 V			1.6	
f _T	Transition frequency	I _C = 1 A V _{CE} = 4 V	2.5			MHz
I _{s/b*}	Second Breakdown Collector Current	V _{CE} = 40 V	2.87			A

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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